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October 2013

FCD4N60

N-Channel SuperFET® MOSFET

600 V, 3.9 A, 1.2 Ω

Features

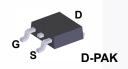
- 650 V @T_J = 150 °C
- Typ. $R_{DS(on)} = 1.0 \Omega$
- Ultra Low Gate Charge (Typ. Q_q = 12.8 nC)
- Low Effective Output Capacitance (Typ. C_{oss}.eff = 32 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

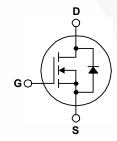
Applications

- · Lighting
- · AC-DC Power Supply
- · Solar Inverter

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol		Parameter		FCD4N60TM	Unit
V_{DSS}	Drain to Source Voltage			600	V
. \	Drain Current	- Continuous (T _C = 25°C)		3.9	^
ID	Diain Current	- Continuous (T _C = 100°C)		2.5	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	11.7	Α
V _{GSS}	Gate to Source Voltage			±30	V
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	128	mJ
I _{AR}	Avalanche Current (Note 1)		(Note 1)	3.9	Α
E _{AR}	Repetitive Avalanche Ene	ergy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/	dt	(Note 3)	4.5	V/ns
D	Dower Dissination	(T _C = 25°C)		50	W
P_{D}	Power Dissipation	- Derate above 25°C		0.4	W/°C
T _J , T _{STG}	Operating and Storage Te	emperature Range		-55 to +150	°C
T _L	Maximum Lead Temperat 1/8" from Case for 5 Seco	ure for Soldering Purpose, onds		300	°C

Thermal Characteristics

Symbol	Parameter	FCD4N60TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	83	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCD4N60	FCD4N60TM	D-PAK	380mm	16m	2500

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
D\/	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS} Drain to Source Brea	Diam to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 150^{\circ}\text{C}$	-	650	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.6	-	V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 3.9 \text{ A}$	-	700	-	V
Zoro Coto Voltago Prain Current		V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	^
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 2.0 \text{ A}$	-	1.0	1.2	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 2.0 A	-	3.2	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	- \	415	540	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ ce $f = 1.0 \text{ MHz}$		210	275	pF
C _{rss}	Reverse Transfer Capacitance			19.5	-	pF
C _{oss}	Output Capacitance	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	-	12	16	pF
C _{oss} eff.	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	-	32	-	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	16	45	ns
t _r	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_{D} = 3.9 \text{ A}$ $R_{G} = 25 \Omega$		45	100	ns
t _{d(off)}	Turn-Off Delay Time			36	85	ns
t _f	Turn-Off Fall Time	(Note 4) -	30	70	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 480 V, I _D = 3.9 A,	-	12.8	16.6	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	/ -	2.4	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4	-	7.1	-	nC

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3.9	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	11.7	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 11 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 11 \text{ A}$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	277	///-	ns
Q _{rr}	Reverse Recovery Charge	dl _F /dt = 100 A/μs	-	2.07	-	μС

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. I $_{AS}$ = 1.9 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C
- 3. I $_{SD} \leq$ 3.9 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS}$, Starting T $_{J}$ = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

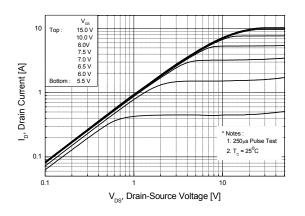


Figure 2. Transfer Characteristics

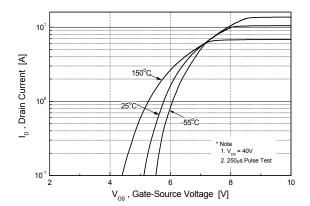


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

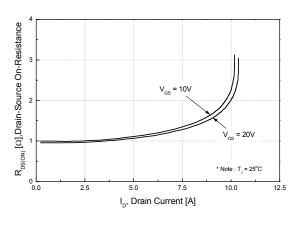


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

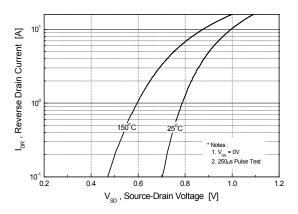


Figure 5. Capacitance Characteristics

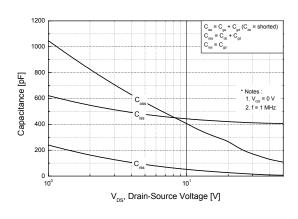
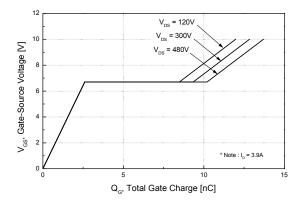


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

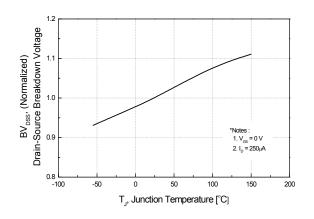


Figure 8. On-Resistance Variation vs. Temperature

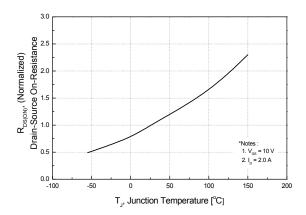
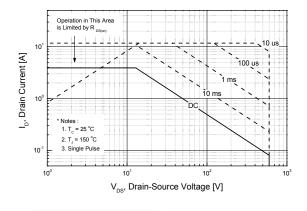


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



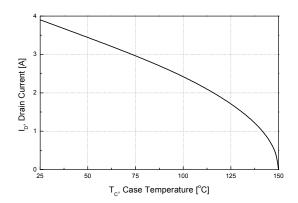


Figure 11. Transient Thermal Response Curve

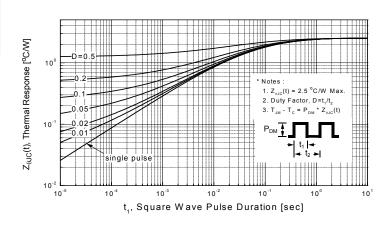


Figure 12. Gate Charge Test Circuit & Waveform

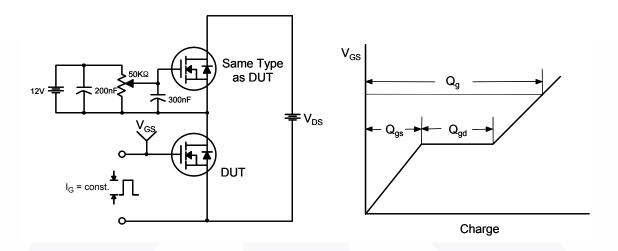


Figure 13. Resistive Switching Test Circuit & Waveforms

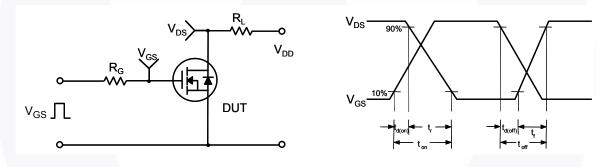
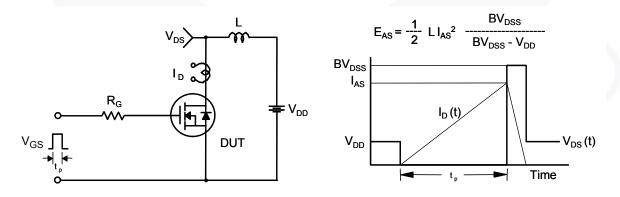


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



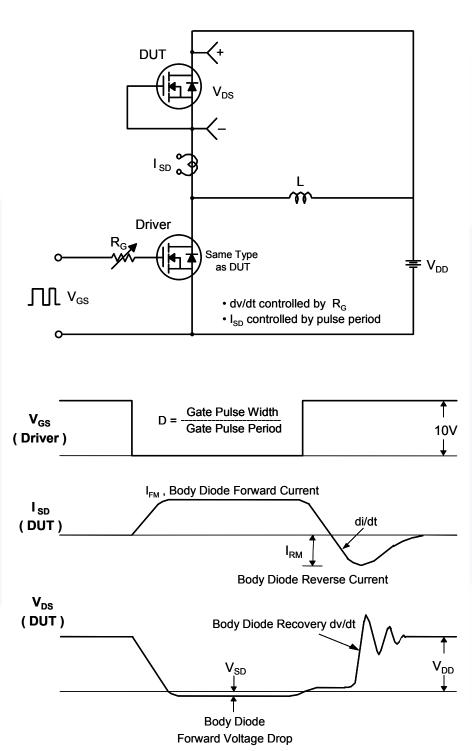


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-252 3L (DPAK)

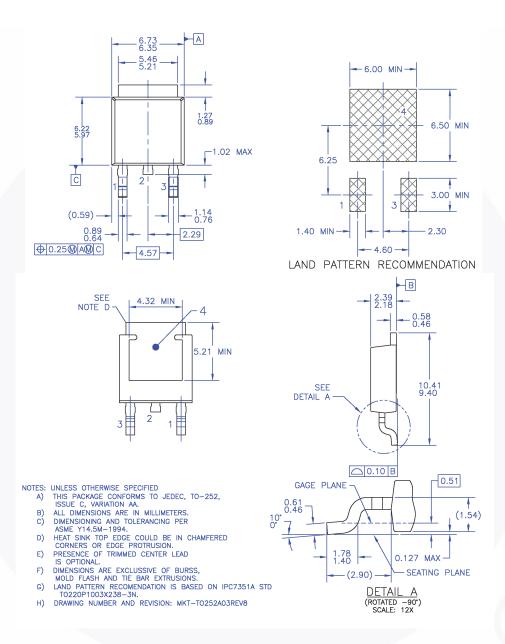


Figure 16. TO252 (D-PAK), Molded, 3 Lead, Option AA&AB

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Dimension in Millimeters





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